**Product data sheet** 

## 1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

### 2. Features and benefits

- Extremely fast switching
- Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET

## 3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute maximum rating							
$V_{RRM}$	repetitive peak reverse voltage			600			V
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; $T_{mb} \le 78$ °C; square-wave pulse; Fig. 1; Fig. 2		10			А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 78 °C; square-wave pulse	20		А		
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	65 71			Α	
	forward current	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			Α		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>		-	1.4	1.8	V
Dynamic	Dynamic characteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$		-	19	-	ns

Hyperfast power diode

# 5. Pinning information

### **Table 2. Pinning information**

K			Graphic symbol
r\	cathode	mb	
A	anode	7 0 1	K — A 001aaa020
mb	mounting base; connected to cathode		001aaa020
_		nb mounting base; connected to	mounting base; connected to cathode

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
		plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

# 7. Marking

### Table 4. Marking codes

	Type number	Marking codes
ſ	BYC10-600	BYC10-600

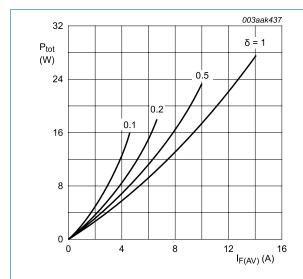
Hyperfast power diode

# 8. Limiting values

#### **Table 5. Limiting values**

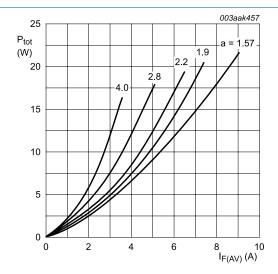
In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Values	Unit
repetitive peak reverse voltage		600	V
crest working reverse voltage		600	V
reverse voltage	T <sub>mb</sub> ≤ 114 °C	500	V
average forward current	$\delta$ = 0.5; T <sub>mb</sub> ≤ 78 °C; square-wave pulse; Fig. 1; Fig. 2	10	А
repetitive peak forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 78 °C; square-wave pulse	20	А
non-repetitive peak	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	65	А
forward current	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	71	А
storage temperature		-40 to 150	°C
junction temperature		150	°C
	voltage crest working reverse voltage reverse voltage average forward current repetitive peak forward current non-repetitive peak forward current storage temperature	$ \begin{array}{c} \text{voltage} \\ \text{crest working reverse} \\ \text{voltage} \\ \text{reverse voltage} \\ \text{average forward current} \\ \text{average forward current} \\ \text{on-repetitive peak forward current} \\ \text{non-repetitive peak forward current} \\ \text{forward current} \\ \text{t}_p = 10 \text{ ms; } T_{j(\text{init})} = 25 \text{ °C; sine-wave pulse} \\ \text{t}_p = 8.3 \text{ ms; } T_{j(\text{init})} = 25 \text{ °C; sine-wave pulse} \\ \text{storage temperature} \\ \end{array} $	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$



$$\begin{split} & I_{\text{F(AV)}} = I_{\text{F(RMS)}} \times \sqrt{\delta} \\ & V_{\text{o}} = 1.300 \text{ V}; \text{ R}_{\text{s}} = 0.050 \text{ }\Omega \end{split}$$
 Fig. 1. Forward power dissipation as a function of average forward current; square waveform;

maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.300 V;  $R_s$  = 0.050  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

Hyperfast power diode

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	Fig. 3	-	-	2	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

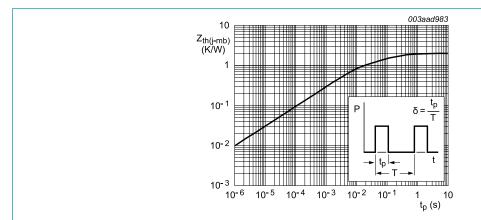


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

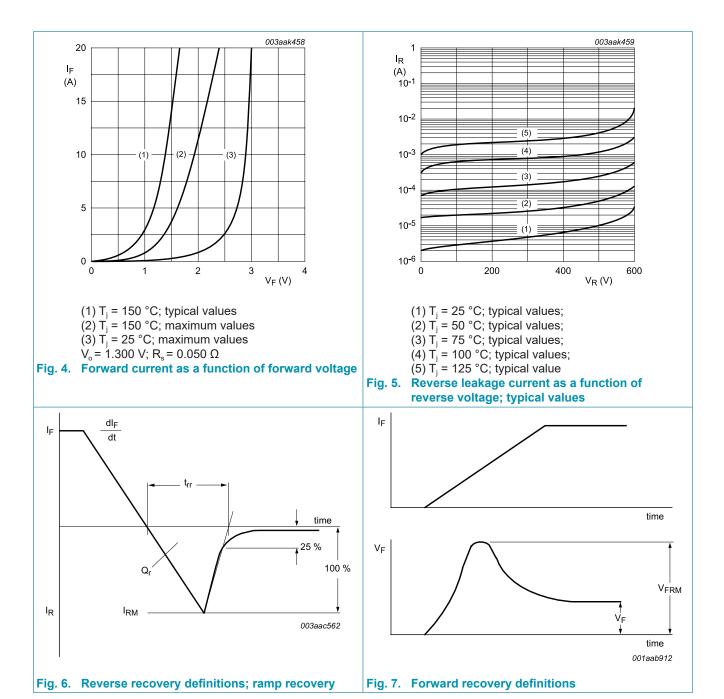
Hyperfast power diode

## 10. Characteristics

### **Table 7. Characteristics**

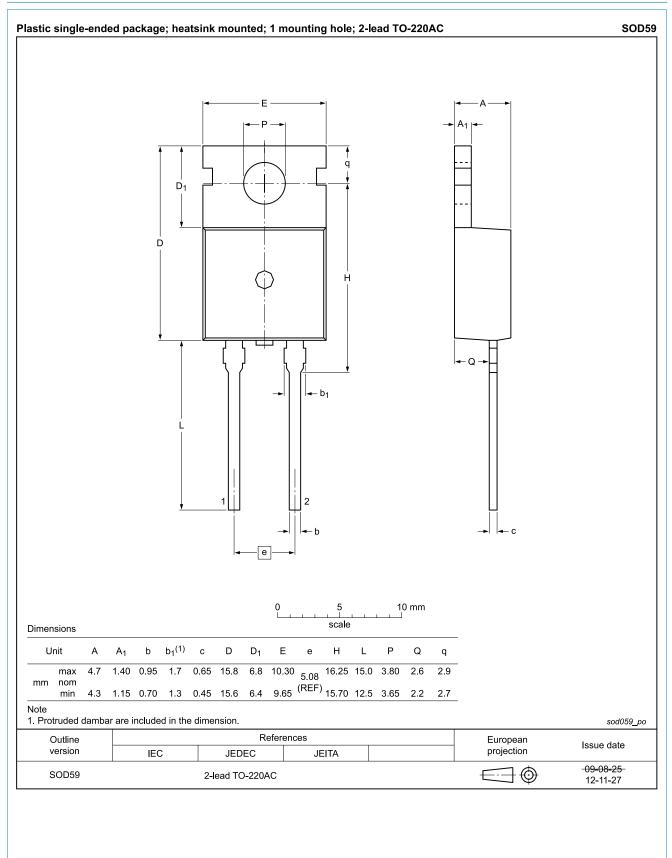
Symbol	Parameter	Conditions	M	in Typ	Max	Unit
Static cha	racteristics				·	
$V_{F}$	forward voltage	I <sub>F</sub> = 10A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	2	2.9	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	1.4	1.8	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	1.7	2.3	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	9	200	μA
		V <sub>R</sub> = 500 V; T <sub>j</sub> = 100 °C; <u>Fig. 5</u>	-	1.1	3	mA
Dynamic	characteristics				'	
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$	-	35	55	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$	-	19	-	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; Fig. 6$	-	32	40	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 6$	-	3	7.5	А
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/µs};$ $T_j = 125 \text{ °C}; Fig. 6$	-	9.5	12	А
V <sub>FRM</sub>	forward recovery voltage	$I_F = 10 \text{ A}; dI_F/dt = 100 \text{ A}/\mu\text{s}; T_j = 25 \text{ °C};$ Fig. 7	-	8	11	V

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# 11. Package outline



### Hyperfast power diode

### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Hyperfast power diode

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Hyperfast power diode

## 13. Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	4
10. Characteristics	5
11. Package outline	7
12. Legal information	8
13. Contents	

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